TO-252 ṂṂ Ḷ ⸗ g͡ ‖ ˥

Schottky Barrier Diode in a TO-252 Plastic Package.

ᴀ* ᵇ ⫤ ⫫ ʹ ˥ ı ʌ Ḥ* ᵇ ʀ ᴗ V_F(typ)=0.2V ı ᴌ ȁ ᴀ □ ᴌ ḧ ớ

High Forward Surge Capability, Ultra Low Forward Voltage Drop V_F(typ)=0.2V, Excellent High Temperature Stability.

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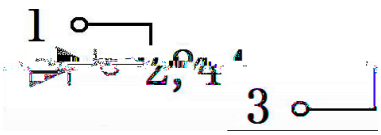
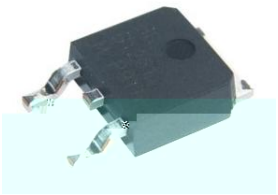
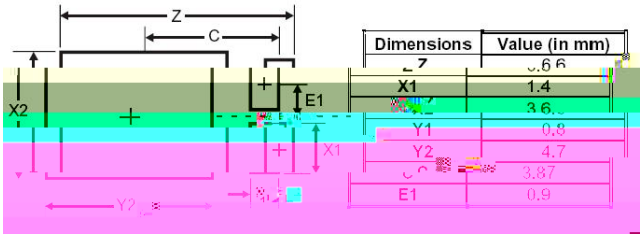
For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.







PIN1 χ Anode PIN 2,4 χ Cathode PIN 3 χ Anode Suggested Pad layout

ȯ ᴍ ˥ ᴗ ˝ See Marking Instructions.

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ӈ Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage Peak Reverse Voltage	V_{RRM} V_{RWM} V_{RM}	45	V
RMS Reverse voltage	$V_{R(RMS)}$	31.5	V
Average Rectified Output Current	I_O	10	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	250	A
Junction Temperature Range	$T_{j\ MAX}$	150	
Storage Temperature Range	T_{stg}	-55˙ 150	
Typical Thermal Resistance	$R_{\theta JA}$ˆ Note 1˜	73	/W

v ̈Ω Parameter	ϒ N Symbol	⊥⊥ ؛ ǂ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	D Ӈ Unit
Reverse Voltage	V_R	I_R=0.5mA	45			V
Forward voltage	V_F	I_F=2A T_J=25		0.33	0.38	V
		I_F=2A T_J=125		0.20		V
		I_F=10A T_J=25		0.42	0.46	V
		I_F=10A T_J=125		0.35		V
Instantaneous Reverse Current	I_Rˆ Note 2˜	V_R=45V T_J=25		0.06	0.12	mA
		V_R=45V T_J=100			12	mA
		V_R=45V T_J=125			50	mA

├2Notes'

41 IU07 SFE ı 5 ´ И ق ı ω Ӈ ấ ɲ ` ṵ ṕ /FR-4 PCB, 2oz. Copper, minimum recommended pad layout per.

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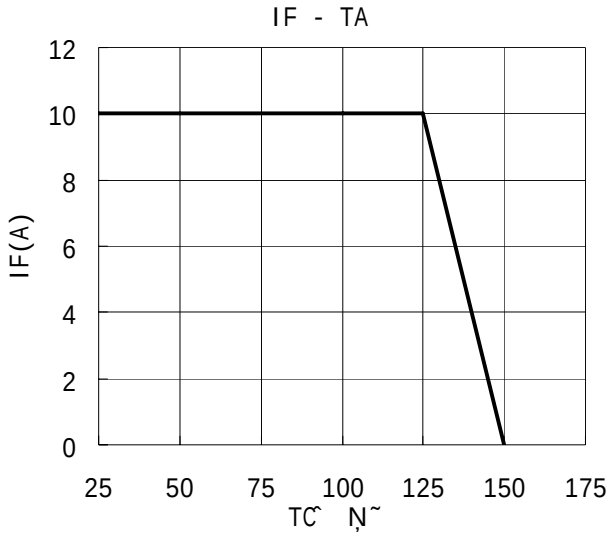
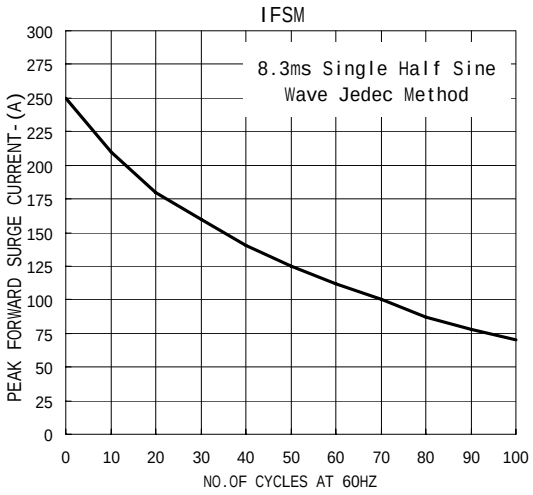
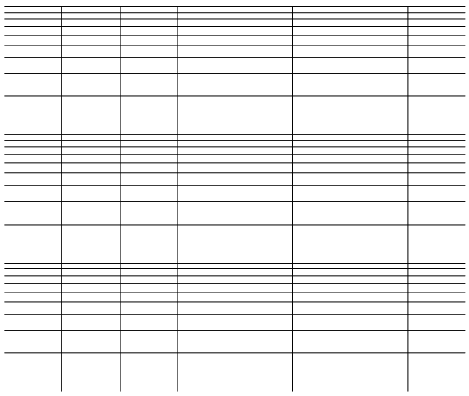
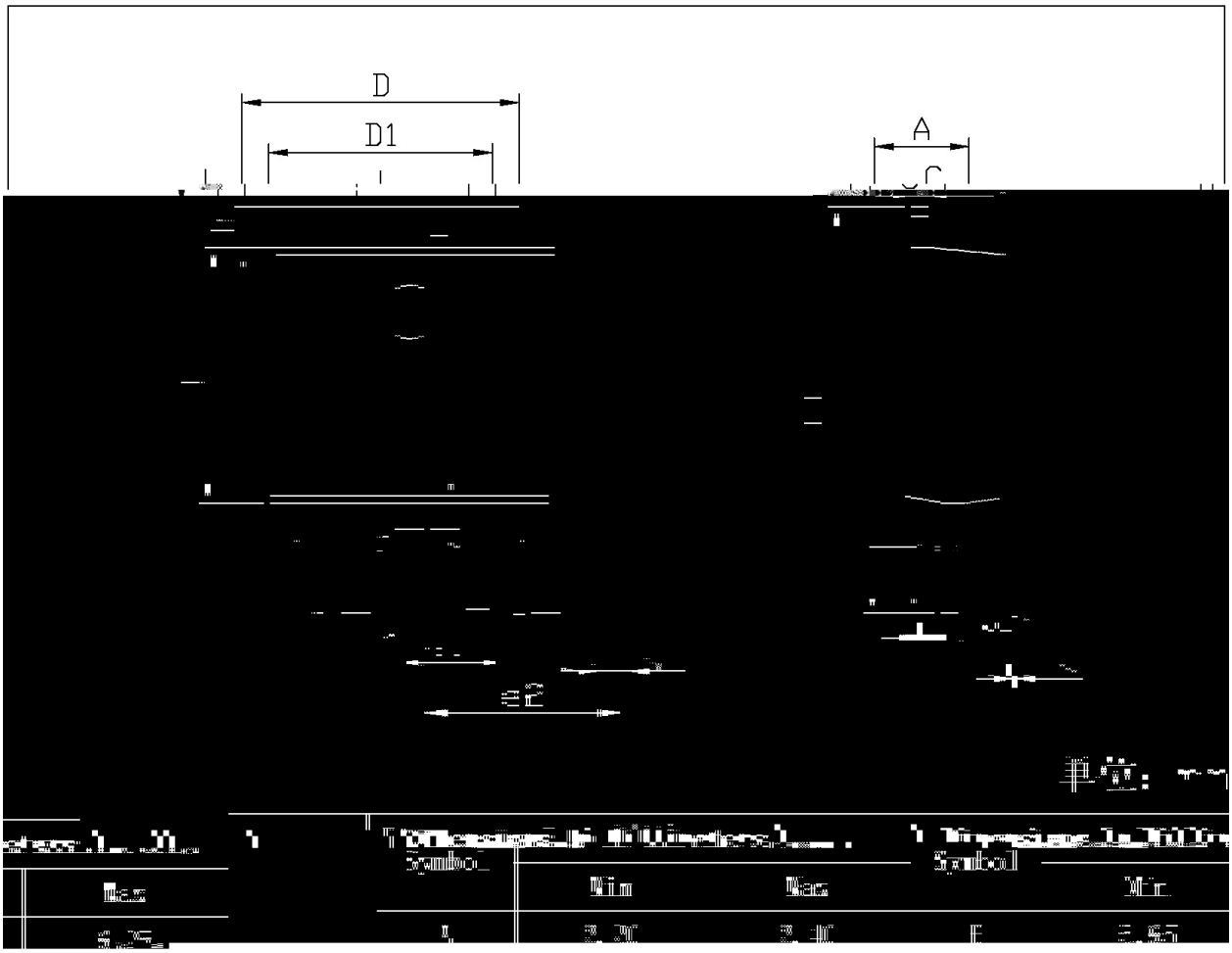

IF - TA
IF(A)
12
10
8
6
4
2
0
25
50
75
100
125
150
175
TC N


IFSM
8.3ms Single Half Sine
Wave Jedec Method
PEAK FORWARD SURGE CURRENT- (A)
300
275
250
225
200
175
150
125
100
75
50
25
0
0
10
20
30
40
50
60
70
80
90
100
NO.OF CYCLES AT 60HZ

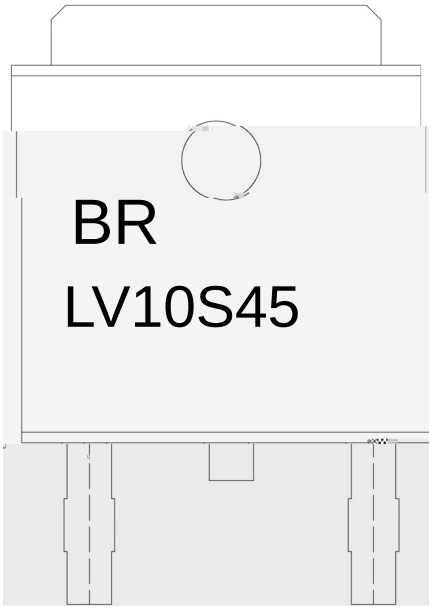




Symbol	Min	Max	Symbol	Min

0.00	0.10	D1	5.10	5.50

TO-252



ب ˝ χ

EU χ	ⱶ ⱷ ᴵ Ⱬ
0Y43V78 χ	ⱶ ⱷ ᴺ Ⱬ
---- χ	ⱶ ⱶ ⱷ ᴴ ᴺ Ⱬ ⱶ ⱶ ⱶ ⱷ ᴴ ᴺ Ⱳ ⱷ

Note:

BR:	Company Code
0Y43V78 χ	Product Type Code.
****:	Lot No. Code, code change with Lot No.